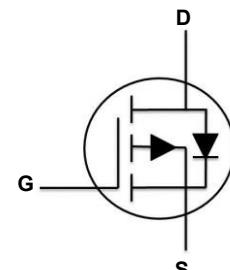
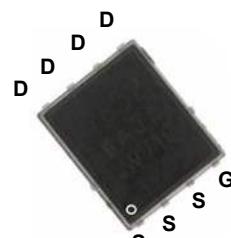


## Main Product Characteristics

$BV_{DSS}$	-30V
$R_{DS(ON)}$	8.6mΩ @-10V (Typ)
	11.8mΩ @-4.5V (Typ)
$I_D$	-64A



PPAK5x6

Schematic Diagram

## Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



## Description

The GSFP0365 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous ( $T_c=25^\circ\text{C}$ )	$I_D$	-64	A
Drain Current-Continuous ( $T_c=70^\circ\text{C}$ )		-51	
Drain Current-Pulsed ( $T_c=25^\circ\text{C}$ ) <sup>1</sup>	$I_{DM}$	-224	A
Single Pulse Avalanche Energy <sup>2</sup>	$E_{AS}$	101	mJ
Power Dissipation ( $T_c=25^\circ\text{C}$ )	$P_D$	56.8	W
Power Dissipation ( $T_c=70^\circ\text{C}$ )		45	W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.2	°C/W
Operating Junction Temperature Range	$T_J$	-50 To +150	°C
Storage Temperature Range	$T_{STG}$	-50 To +150	°C

**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>On / Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30	-	-	V
Zero Gate Voltage Drain Current ( $T_C=25^\circ\text{C}$ )	$I_{\text{DSS}}$	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	$\mu\text{A}$
Zero Gate Voltage Drain Current ( $T_C=125^\circ\text{C}$ )		$V_{\text{DS}}=-24\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-100	$\mu\text{A}$
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm100$	nA
Static Drain-Source On-Resistance <sup>3</sup>	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-15\text{A}$	-	8.6	12	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-10\text{A}$	-	11.8	16	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{GS}}=V_{\text{DS}}, I_{\text{D}}=-250\mu\text{A}$	-1.0	-1.5	-2.5	V
<b>Dynamic and Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-15\text{A}$ $V_{\text{GS}}=-10\text{V}$	-	64.3	-	nC
Gate-Source Charge	$Q_{\text{gs}}$		-	6.9	-	
Gate-Drain Charge	$Q_{\text{gd}}$		-	16.5	-	
Turn-On Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=-15\text{V}, R_{\text{G}}=6\Omega$ $V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-1\text{A}$	-	12	-	nS
Rise Time	$t_r$		-	41.8	-	
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	80	-	
Fall Time	$t_f$		-	19.5	-	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V},$ $F=1\text{MHz}$	-	1360	-	pF
Output Capacitance	$C_{\text{oss}}$		-	373	-	
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	137	-	
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Diode Forward Voltage <sup>3</sup>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_{\text{SD}}=-15\text{A},$ $T_J=25^\circ\text{C}$	-	-0.85	-1.2	V

Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2.  $V_{\text{GS}}=10\text{V}, L=0.3\text{mH}, I_{\text{AS}}=26\text{A}, R_{\text{G}}=25\Omega$ , starting  $T_J=25^\circ\text{C}$ .
3. Pulse test: pulse width  $\leqslant 300\text{us}$ , duty cycle  $\leqslant 2\%$ .

## Typical Electrical and Thermal Characteristic Curves

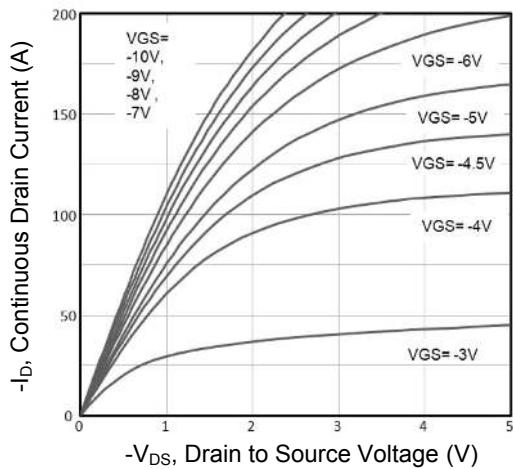


Figure 1. Typical Output Characteristics

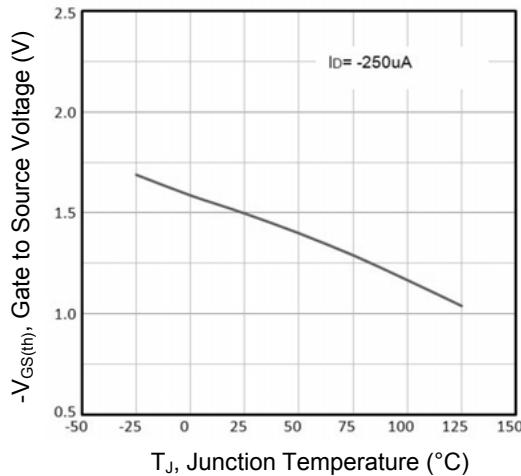


Figure 2. Normalized Threshold Voltage vs.  $T_J$

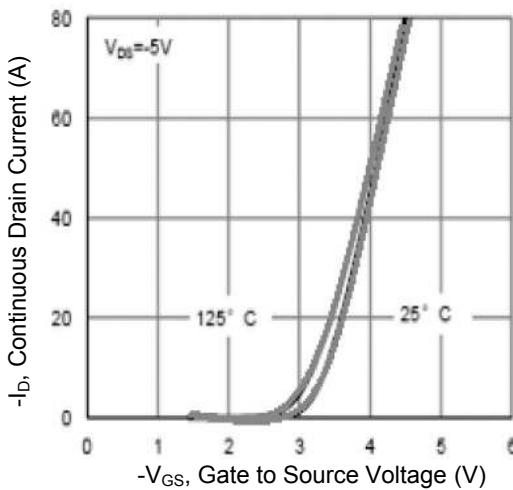


Figure 3. Typical Transfer Characteristics

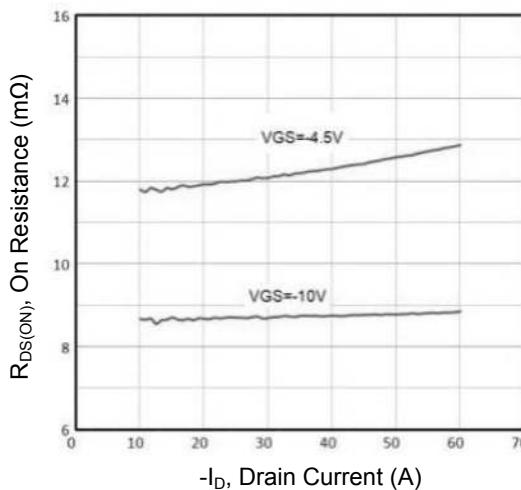


Figure 4. On Resistance vs. Drain Current

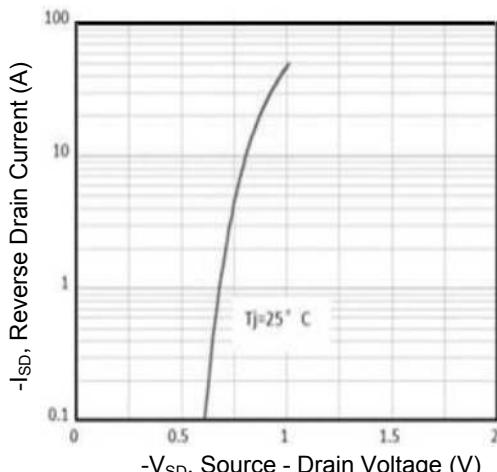


Figure 5. Typical Source - Drain Diode Forward Voltage

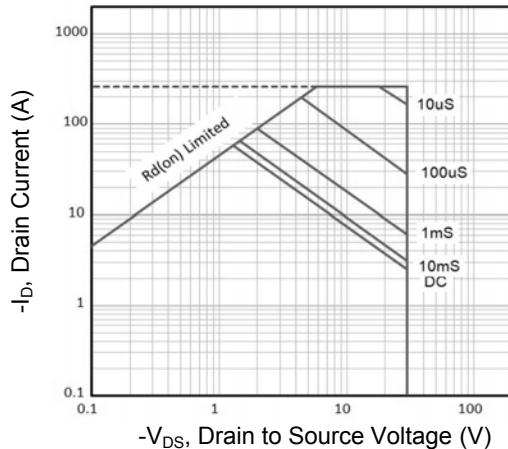


Figure 6. Maximum Safe Operating Area

## Typical Electrical and Thermal Characteristic Curves

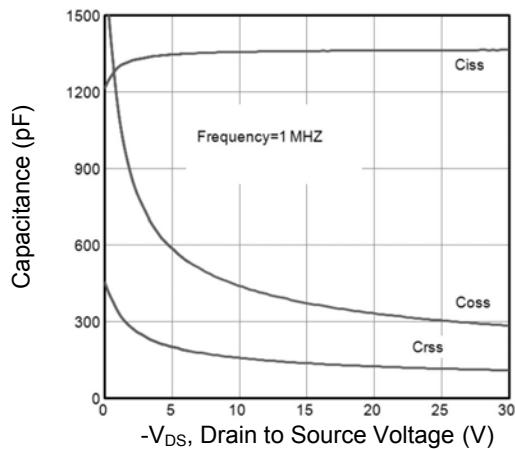


Figure 7. Capacitance Characteristics

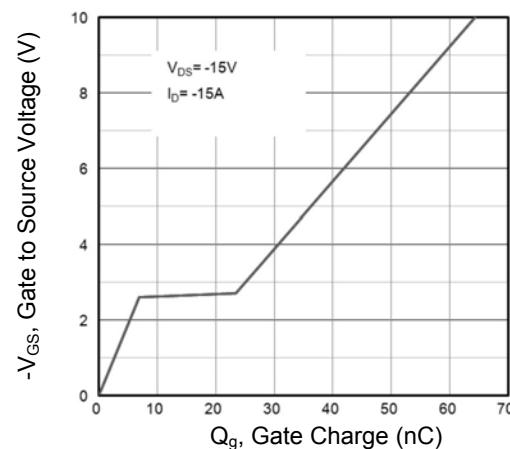


Figure 8. Gate Charge Characteristics

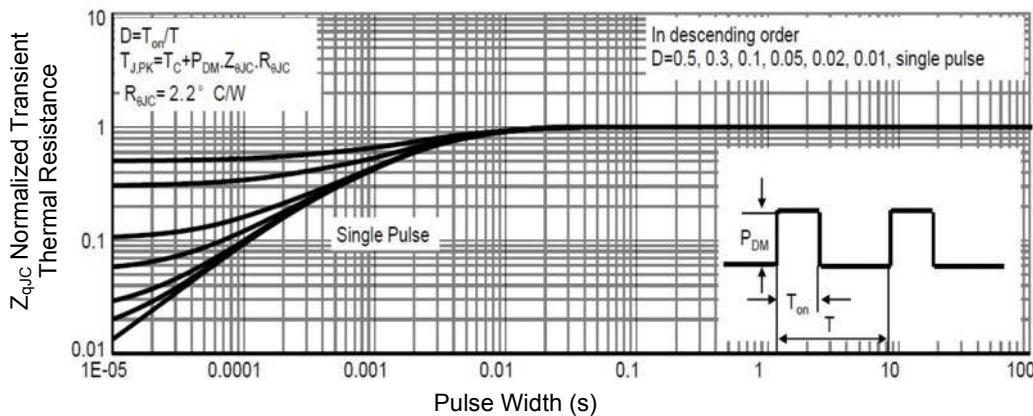


Figure 9. Normalized Maximum Transient Thermal Impedance

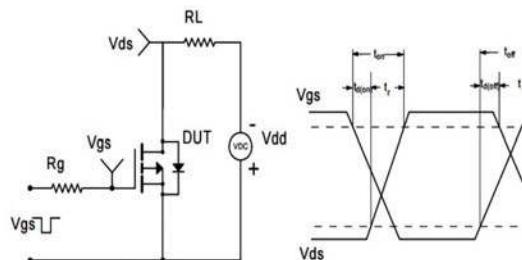


Figure 10. Switching Time Test Circuit and Waveforms

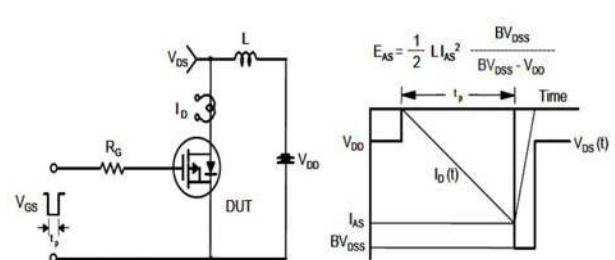
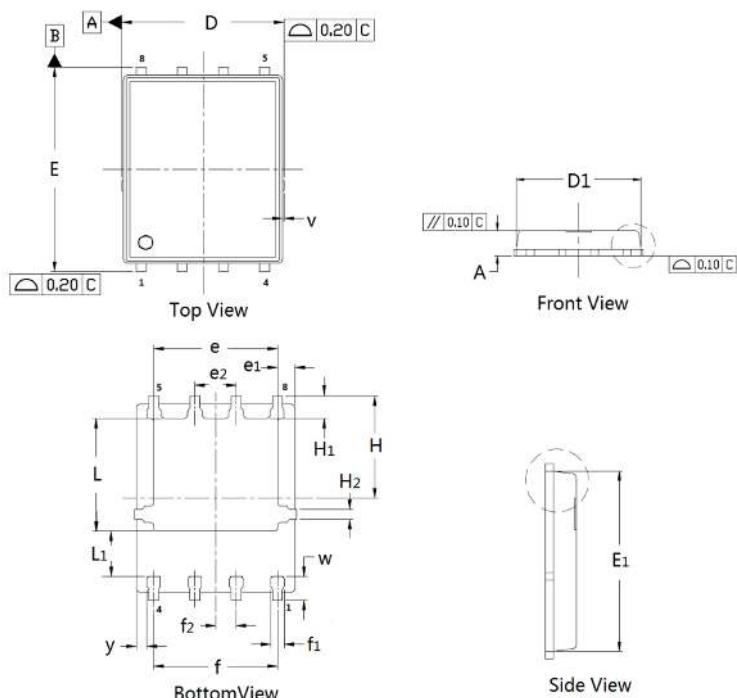


Figure 11. Unclamped Inductive Test Circuit and Waveforms

## Package Outline Dimensions (PPAK5x6)



Symbol	Dimensions in Millimeters			Symbol	Dimensions in Millimeters		
	Min	Typ	Max		Min	Typ	Max
<b>A</b>	0.90	1.05	1.20	<b>D</b>	4.90	5.10	5.30
<b>D<sub>1</sub></b>	4.80	4.89	5.00	<b>E</b>	6.00	6.15	6.30
<b>E<sub>1</sub></b>	5.65	5.74	5.85	<b>e</b>	3.72	3.80	3.92
<b>e<sub>1</sub></b>	-	0.54	-	<b>e<sub>2</sub></b>	-	1.27	-
<b>f</b>	-	3.82	-	<b>f<sub>1</sub></b>	0.31	0.37	0.51
<b>f<sub>2</sub></b>	-	0.64	-	<b>H</b>	-	3.15	-
<b>H<sub>1</sub></b>	0.59	0.63	0.79	<b>H<sub>2</sub></b>	0.26	0.28	0.32
<b>L</b>	3.38	3.45	3.58	<b>L<sub>1</sub></b>	-	1.39	-
<b>v</b>	-	0.13	-	<b>w</b>	0.64	0.68	0.84
<b>y</b>	-	0.34	-				

## Order Information

Device	Package	Marking	Carrier	Quantity
GSFP0365	PPAK5x6	010P03	Tape & Reel	5,000 pcs / Reel